SHI LING®

ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

Specifcation of products

：

：MFK200U12K2

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PRODUCT

- y Ultrafast Rever
- y Soft Reverse Reco
- y Low Reverse Recovery
- y Low Forward Voltage
- y High Surge Current Capability
- y Low Inductance Package

APPLICATIONS

- y Inversion Welder
- y Uninterruptible Power Supply (UPS)
- y Plating Power Supply
- y Ultrasonic Cleaner and Welder
- y Converter & Chopper
- y Power Factor Correction (PFC) Circuit

ABSOLUTE MAXIMUM RATINGS

T_C=25 nless otherwise specified

Symbol	Parameter	Test Conditions	Values	Unit =25
		=100 , Per Moudle		

ELECTRICAL CHARACTERISTICS

T_C=25 unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{RM}	Reverse Leakage Current	V_R=1200V	--	--	1	mA
		V_R=1200V, Ţ=125	--	--	8	mA
V_F	Forward Voltage	I_F=100A	--	2.0	--	V
		I_F=100A, T_J=125	--	1.7	--	V
t_{rr}	Reverse Recovery Time	I_F=1A, V_R=30V, di_F/dt=-200A/μs	--	60	--	ns
t_{rr}	Reverse Recovery Time	V_R=600V, I_F=100A	--	140	--	ns
I_{RRM}	Max. Reverse Recovery Current	di_F/dt=-200A/μs, T_J=25	--	29	--	A
t_{rr}	Reverse Recovery Time	V_R=600V, I_F=100A	--	250	--	ns
I_{RRM}	Max. Reverse Recovery Current	di_F/dt=-200A/μs, T_J=125	--	48	--	A

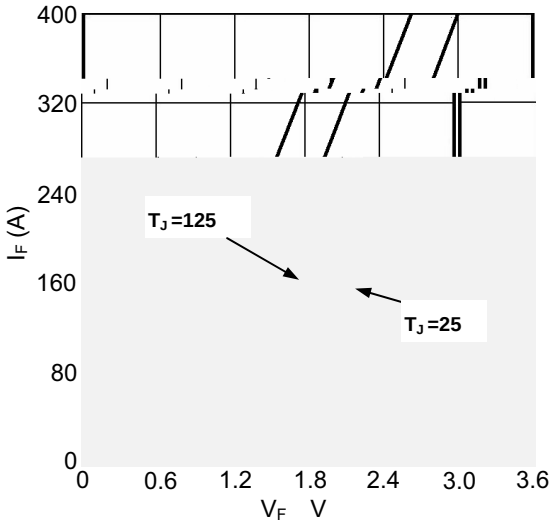


Figure1. Forward Voltage Drop vs Forward Current

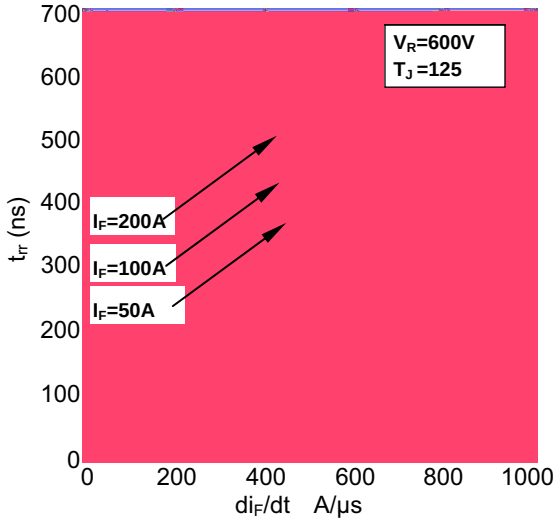


Figure2. Reverse Recovery Time vs di_F/dt

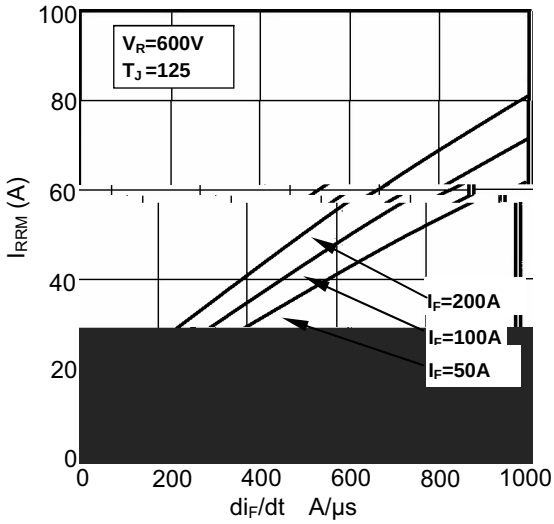


Figure3. Reverse Recovery Current vs di_F/dt

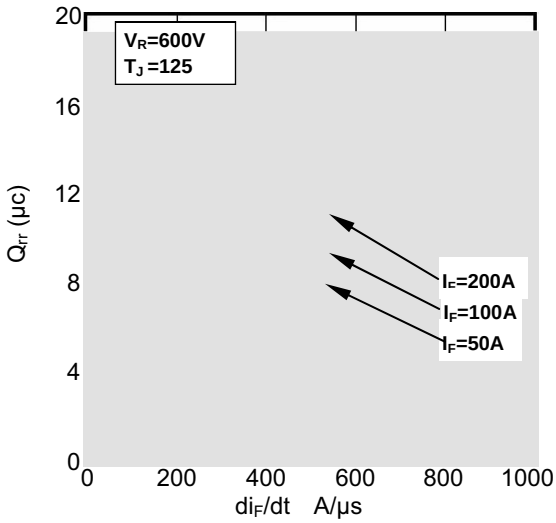


Figure4. Reverse Recovery Charge vs di_F/dt

